

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLW86** is Designed for
Class C, 28 V High Band Applications
up to 175 MHz.

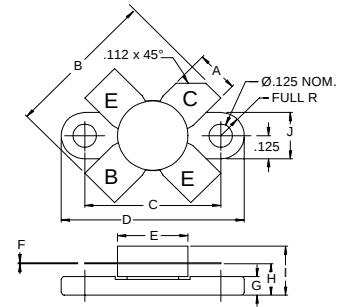
FEATURES:

- Common Emitter
- $P_G = 7.0$ dB at 40 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CBO}	65 V
V_{CE0}	35 V
V_{EBO}	4.0 V
P_{DISS}	60 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	2.9°C/W

PACKAGE STYLE .380 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{CES}	$I_C = 200$ mA	65			V
BV_{CBO}	$I_C = 10$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			1.0	mA
I_{CES}	$V_{CE} = 30$ V			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	5.0		200	---
C_{ob}	$V_{CB} = 30$ V $f = 1.0$ MHz			65	pF
P_G η_c	$V_{CE} = 28$ V $P_{IN} = 7.0$ W $f = 175$ MHz	7.6	60		dB %